13 Nov. (Tuesday)

9:00

PL2
SPIN MAPPING ON THE ATOMIC SCALE
Roland Wiesendanger, Hamburg, Germany

Room A

13Aa
Surface/Interface Structures & Properties-Structures and Diamond-

10:00

13Aa-1,2 Fundamental Limits in the Growth of Si Nanowires (Invited)
James Hannon, Yorktown Heights, NY, USA

13Aa-3,4 Density anomalies at solid-liquid interfaces (Invited)
Harald Reichert, Stuttgart, Germany

11:00

13Aa-5 Density Functional Theory - based calculation on dissociation pathways of SO2 on Copper surface
Mohammad Kemal Agusta, Osaka, Japan

13Aa-6 Theoretical study on hydrogen termination dependence of Schottky barrier height for Al/diamond (100) interfaces
Hiroyuki Kageshima, Atsugi, Japan

13Aa-7 Core level photoelectron spectroscopic study on oxidized phosphorus-doped (111) and (100) diamond surfaces after vacuum-annealing
Kumaragurubaran Somu, Tsukuba, Japan

12:00

13Aa-8 X-ray Photoelectron Analysis of Diamondlike Carbon (DLC) Films with Different Electric Resistivities
Susumu Takabayashi, Higashi-Hiroshima, Hiroshima, Japan

Room B

13Ba
Nano-Magnetism

13Ba-1,2 Recent Progress in Spin-Polarized Scanning Electron Microscopy (Invited)
Kazuyuki Koike, Sapporo, Japan

13Ba-3 Spin-splitting States of Bi-Ag Ordered Surface Alloy on Ag Quantum Well Films
Ke He , Kashiwa, Japan

13Ba-4 Surface structure of epitaxially grown Mn5Ge3 islands on Ge(001) surface
Howon Kim, Seoul, Korea

13Ba-5 Mixed Layer Formation of Copper Overlayers on Ni(110) Surface
Tsuneo Fukuda, Osaka, JAPAN

13Ba-6 Arrangement of Ni3S3 Clusters Formed by Sulfur Adsorption on Ni(111)
Masamichi Yamada, Kashiwa, Japan

13Ba-7 DFT study for ferromagnetic thin film of iron siliside on Si(111) surface
Akira Ishii, Tottori-City, Japan

Room C

13Ca
Thin Film Growth & Application

13Ca-1,2 Large scale electronic structure calculation theory and application to nanostructure materials (Invited)
Takeo Fujiwara, Tokyo, Japan

13Ca-3 The theory of quantum dot formation of InAs/GaAs(001) using the the kinetic Monte Carlo simulation based on the DFT calculation
Akira Ishii, Tottori-City, Japan

13Ca-4 Atomic structure of epitaxially grown Sb irradiated GaAs(001) surface using the first principles calculation
Akira Ishii, Tottori-City, Japan

13Ca-5 Selective growth of stacked InAs quantum dots by using the templates formed by the Nano-Jet Probe
Shunsuke Ohkouchi, Tsukuba, Japan

13Ca-6,7 Viability of a new type of superlattice: periodic repetition of inversion domain boundaries in SiC (Invited)
Peter Deak, Bremen, Germany

13Ca-8 Impact of surface step-heights of 6H-SiC (0001) vicinal substrates in heteroepitaxial growth of 2H-AlN
Hironori Okumura, Kyoto, Japan

13:00

Lunch

Room A

13Ap1
Thin Film Growth and Application

13:30

13Ap1-1,2 Giant Tunneling Magnetoresistance in MgO-based Magnetic Tunnel Junctions and Its Applications to Spintronic Devices (Invited)
Shinji Yuasa, Tsukuba, Japan

14:00

13Ap1-3 Size and distribution control of Co nano clusters grown by arc plasma gun
Toshio Kawahara, Ibaraki, Japan

13Ap1-4 Super high-brightness spin-polarized transmission photocathode based on a GaAs/GaAsP strained superlattice structure on a GaP substrate
XiuGuang Jin, Nagoya, Japan

13Ap1-5 Polarization improvement of spin-polarized electrons from strain-compensated GaAs/GaAsP superlattice photocathode
Takanori Kato, Nagoya, Japan

13Ap1-6 An Extreme Change in structural and optical properties of Indium Oxynitride deposited by reactive gas-timing r.f. magnetron sputtering
Apichart Sungthong, Bangkok, Thailand

15:00

13Ap1-7 Photomodulated Reflectance Study on Optical Property of InN Thin Films Grown by Reactive Gas-Timing RF Magnetron Sputtering
Supanit Porntheeraphat, Prathumtani, Thailand

13Ap1-8 DFT study for growth of GaN and ZnO on non-polar surfaces of GaN and ZnO
Yasuhiro Oda, Tottori-City, Japan

Room B

13Bp1
Scanning Probe Microscopy

13Bp1-1,2 What is different in One-dimensional systems? (Invited)
Young Kuk, Seoul, Korea

13Bp1-3 STM observation of 2D electronic states on Si(111)-beta-root 3 x root 3-Bi surface
Katsumi Nagaoka, Ibaraki, Japan

13Bp1-4 STM observation and photoemission spectroscopy of Mn adsorbed Si(111) r3*r3-Ag surface
Keiko Takase, Tokyo, Japan

13Bp1-5 Mapping of the Superconducting Gap in Nano-size Pb Islands using Scanning Tunneling Microscopy/Spectroscopy
Takahiro Nishio, Kashiwa, Japan

13Bp1-6 Visualizing Local Gate Control in a Inter-Nanowire Junction Transistor
Jin-Hyung Lim, Seoul, Korea

13Bp1-7 Spatial imaging of valence band electronic structures in a GaSb/InAs quantum well
Kyoichi Suzuki, Kanagwa , Japan

13Bp1-8 Characterization of In adatom induced local states at InAs(111)A surface
Kiyoshi Kanisawa, Atsugi, Japan

Room C

13Cp1
Reaction & Dynamics

13Cp1-1,2 Atomic Scale Surface Dynamics Studies Using Helium-3 Spin Echo (Invited)
Andrew Jardine, Cambridge, U.K.

13Cp1-3 A Monte Carlo simulation study of H2 layers on NaCl (001)
Abdulwahab Sallabi, Misurata, Libya

13Cp1-4 First-Principles Methods for High-Speed and Highly-Charged Ion Irradiation on Solid Surfaces
Yoshiyuki Miyamoto, Tsukuba, Japan

13Cp1-5 Adsorption of acetic acid on the Si(001)-2x1 surface
Takenori Kawaguchi, Hamamatsu, Japan

13Cp1-6 Temperature Controlled Cycloaddition of Alkene on Si(100) Surface
Kazuto Akagi, Tokyo, Japan

13Cp1-7 Development of Reaction Time Accelerated Molecular Dynamics for Large-Scale Chemical Reaction Systems
Hiromitsu Takaba, Sendai, Japan

13Cp1-8 Synthesis and Utilization of Mg/Al Hydrotalcite for Removing Dissolved Humic Acid
Sri Juari Santosa, Yogyakarta, Indonesia

Room A

13Ap2
Thin Film Growth and Application

16:00

13Ap2-1 Influence of solution pH on the electrochemical fabrication of functional metal oxides using a nano-porous alumina template
Jaeyoung Lee, Gwangju, South Korea

13Ap2-2 Molecular beam epitaxy of semiconductor(BaSi2)/metal(CoSi2) hybrid structures on Si(111) substrates for photovoltaic application
Yoshitake Ichikawa, Tsukuba, Japan

13Ap2-3 Electroluminescence of nanostructured Si layers in a 0.9-1.6 mu m range
Alexander Shklyaev, Tokyo, Japan

13Ap2-4 Formation of high-density Si nanodots and characterization of chemical bonding states by soft-X-ray photoelectron spectroscopy
Hiroki Kondo, Nagoya, JAPAN

17:00

13Ap2-5 General Kinetic Theory for Thermal Oxidation of Silicon
Takanobu Watanabe, Tokyo, Japan

13Ap2-6 Photoassisted STM/STS Study of the Local Electronic Properties of a Thin HfO2/Si Structure
Noriyuki Miyata, Tsukuba, Japan

13Ap2-7 Elimination of GeO2 interfacial transition regions and defects at n-type Ge interfaces a pathway for formation of nMOS devices on Ge substrates
Gerald Lucovsky, Raleigh, NC, USA

13Ap2-8 Photochemical reaction of ozone and 1,1,1,3,3,3-hexamethyldisilazane (HMDS): Analysis on the gaseous reaction between precursors of a photo-CVD process
Ken Nakamura, Tsukuba, Ibaraki, Japan

Room B

13Bp2
Nano-Biotechnology

13Bp2-1,2 Supported Bilayer Membranes (Invited)
Stephen Evans, Leeds, UK

13Bp2-3,4 Fracture Mechanics of Proteins and Protein Based Structures (Invited)
Atsushi Ikai, Yokohama, Japan

13Bp2-5 Profiling Protein Surface Interactions of Multicomponent Suspensions via Flow Cytometry
Darby Kozak, St. Lucia, Australia

13Bp2-6 Tailoring of electronic and transport properties in biological systems
Denis Vyalikh, Dresden, Germany

13Bp2-7 Comparison of Modified Biopolymers on Non-Specific Protein Adsorption for a Novel Microsphere Immunoassay
Annie Chen, Brisbane, Australia

13Bp2-8 Elasticity of the Purple Membrane Measured by Atomic Force Microscopy
Koji Sumitomo, Atsugi, Japan

Room C

13Cp2
Reaction & Dynamics

13Cp-1,2 Structure and Reaction at Metal-Water Interfaces (Invited)
Osamu Sugino, Kashiwa, Japan

13Cp2-3 Synthesis of Al-catalyzed Si nanowires through removal of anodized aluminum oxide (AAO) directly formed on Si
Jin-Young Jung, Ansan, Korea

13Cp2-4 Rate of Kink Generation at Steps on Si(111) Surfaces During Wet Etching
Ryu Hasunuma, Tsukuba, Japan

13Cp2-5 Synthesis of SiGe nanoparticles using GeCl4 gas on a silicon wafer
Kwang-Tae Park, Ansan, Korea

13Cp2-6 Development of Porous Structure Simulator for Multi-Scale Simulation of Complex Porous Materials
Michihisa Koyama, Sendai, Japan

13Cp2-7 Time resolved O1s & Si2p XPS for oxidation of Si(111)-7x7 at 300K
Akitaka Yoshigoe, Kouto, Japan

13Cp2-8 Hybrid-DFT study for the initial oxidation steps on silicon cluster surface
Kenji Imamura, Tokyo, Japan

18:00

Poster Session 2

19:00